



Op 2812

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chandra V. Mouli § Group Art Unit: 2812
Serial No.: 09/379,092 §
Filed: August 23, 1999 § Examiner: R. Pompey
For: FORMING SIDEWALL OXIDE §
LAYERS FOR TRENCH §
ISOLATION § Atty. Dkt. No.: MICT-0042-US

8/a
G. Stanley
4-27-01

Commissioner for Patents
Washington DC 20231

REPLY TO PAPER NO. 7

Sir:

In response to the office action mailed March 28, 2001,
please amend the above-referenced patent application as follows:

In the Claims:

Please amend claim 1 as follows:

1. (Amended) A method of forming a trench isolation
comprising:

a) forming a region containing oxidation enhancing
impurities in a semiconductor structure by implanting impurities
which enhance the oxidation of said structure beyond that which
would be expected from crystallographic damage effects; and

making a trench through said region, leaving a portion
of said region around said trench.

Please cancel claim 4.

Please amend claim 5 as follows:

5. (Amended) The method of claim 1 further including
implanting argon.

Cut [Please amend claim 6 as follows:]

Date of Deposit: 4-19-01

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